L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:41
2	1974	(memory or storage) and cell with float$5 not gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:42
3	130	((memory or storage) and cell with float$5 not gate) and cell with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:47
4	32	(((memory or storage) and cell with float$5 not gate) and cell with transistor) and pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:43
5	98	(((memory or storage) and cell with float$5 not gate) and cell with transistor) not ((((memory or storage) and cell with float$5 not gate) and cell with transistor) and pulse)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:47

L Number	Hits	Search Text	DB	Time stamp
1	2732731	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:03
2	1974	(memory or storage) and cell with float$5 not gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:20
3	130	((memory or storage) and cell with float$5 not gate) and cell with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:47
4	32	(((memory or storage) and cell with float$5 not gate) and cell with transistor) and pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:43
5	98	(((memory or storage) and cell with float$5 not gate) and cell with transistor) not ((((memory or storage) and cell with float$5 not gate) and cell with transistor) and pulse)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:47
6	274	((memory or storage) and cell with float$5 not gate) and (static or sram)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:53
7	8	(((memory or storage) and cell with float$5 not gate) and (static or sram)) and 365/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:54
8	54	((memory or storage) and cell with float$5 not gate) and 365/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 14:54
9	805	(memory or storage) and cell with transistor with open	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:08
10	430	((memory or storage) and cell with transistor with open) and 365/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:13
11	36	((memory or storage) and cell with transistor with open) and 365/154.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:13
12	7681	(memory or storage) and cell with (source or drain) with float$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:31
13	3944	((memory or storage) and cell with (source or drain) with float$5) and 365/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:25
14	41	((memory or storage) and cell with (source or drain) with float$5) and 365/154.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:25
15	3198	(memory or storage) and cell with transistor with (source or drain) with float$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:51

16	94	((memory or storage) and cell with transistor with (source or drain) with float$5) and source with electrically adj floating	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:33
17	30	(((memory or storage) and cell with transistor with (source or drain) with float$5) and source with electrically adj floating) and pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:52
18	465	((memory or storage) and cell with transistor with (source or drain) with float$5) and pulse with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/01 15:53